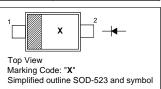
SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for high speed switching circuit and small current rectification applications

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Average Forward Current	Io	200	mA
Non-repetitve Peak Forward Surge Current	I _{FSM}	1	А
Junction Temperature	T _j	125	°C
Storage Temperature Range	Ts	- 40 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 200 mA	V_{F}	0.5	V
Reverse Current at $V_R = 10 \text{ V}$	I _R	30	μΑ



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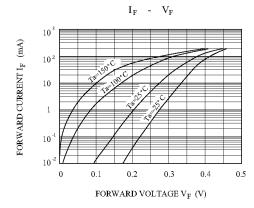
(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)

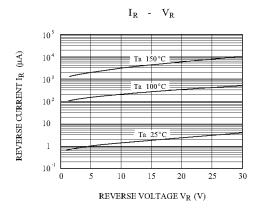


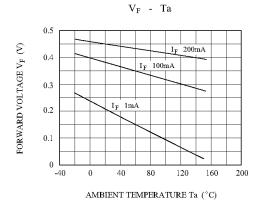


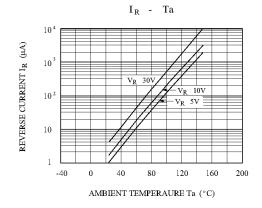


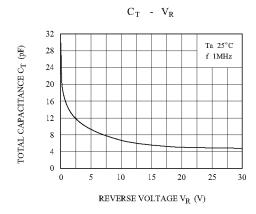
Dated: 06/12/2006













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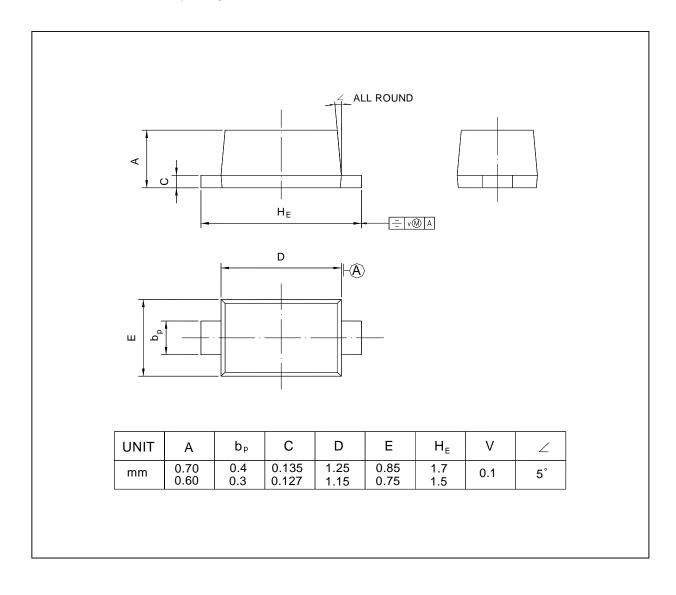


Dated: 06/12/2006

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523





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Dated: 06/12/2006